

FZT751Q

#### **60V PNP HIGH PERFORMANCE TRANSISTOR IN SOT223**

#### **Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

#### **Features**

- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -3A High Continuous Current
- I<sub>CM</sub> = -6A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -300mV @ -1A</li>
- Complementary NPN Type: FZT651Q
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Applications**

- Automotive Lighting
- MOSFET and IGBT Gate Driving

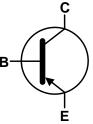
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

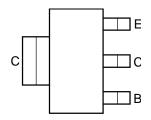
SOT223



Top View



Device Symbol



Top View Pin-Out

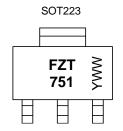
#### Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FZT751QTA	Automotive	FZT751	7	12	1,000
FZT751QTC	Automotive	FZT751	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

### **Marking Information**



FZT 751 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 8 = 2018) WW or  $\overline{W}W$  = Week Code (01 to 53)



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I <sub>CM</sub>	-6	Α

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	0	2	W
Power Dissipation	(Note 7)	P <sub>D</sub>	3	W
Thermal Resistance, Junction to Ambient	(Note 6)	2	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	12.9	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

# ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

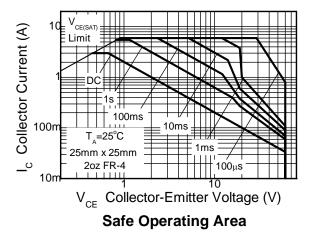
- 6. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.

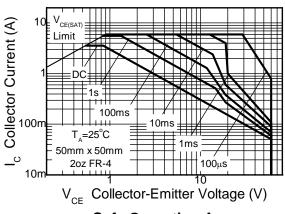
  8. Thermal resistance from junction to solder-point (at the end of the collector lead).

  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

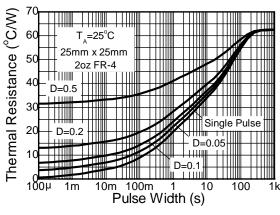


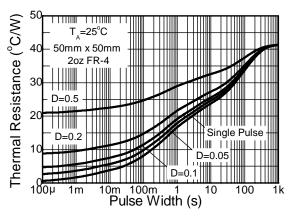
# **Thermal Characteristics and Derating Information**





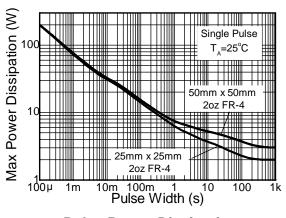
**Safe Operating Area** 

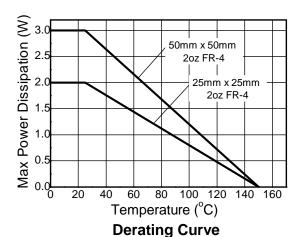




**Transient Thermal Impedance** 

**Transient Thermal Impedance** 





**Pulse Power Dissipation** 



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-80	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-60	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	_	V	$I_E = -100 \mu A$
Collector Cut-off Current		_	<-1	-100	nA	V <sub>CB</sub> = -60V
Collector Cut-on Current	I <sub>CBO</sub>	_	_	-10	μΑ	$V_{CB} = -60V, T_A = +100^{\circ}C$
Emitter Cut-off Current	I <sub>EBO</sub>	_	<-1	-100	nA	$V_{EB} = -4V$
Collector Emitter Seturation Voltage (Note 10)	\/	_	-0.15	-0.3	V	$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(SAT)}$	_	-0.45	-0.6	V	$I_C = -3A$ , $I_B = -300mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(SAT)</sub>	_	-0.9	-1.25	V	$I_C = -1A$ , $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(ON)</sub>	_	-0.8	-1.0	V	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
		70	200	_		$I_C = -50 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Coin (Note 10)	L	100	200	300		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 10)	h <sub>FE</sub>	80	170	_	_	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
		40	150	_		$I_C = -2A$ , $V_{CE} = -2V$
Current Gain-Bandwidth Product	f <sub>T</sub>	100	140	_	MHz	$V_{CE} = -5V, I_{C} = -100mA$ f = 100MHz
Turn-On Time	t <sub>ON</sub>	_	40	_	ns	V <sub>CC</sub> = -10V, I <sub>C</sub> = -500mA
Turn-Off Time	t <sub>OFF</sub>	_	450	_	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Output Capacitance	Сово	_	_	30	pF	V <sub>CB</sub> = -10V, f = 1MHz

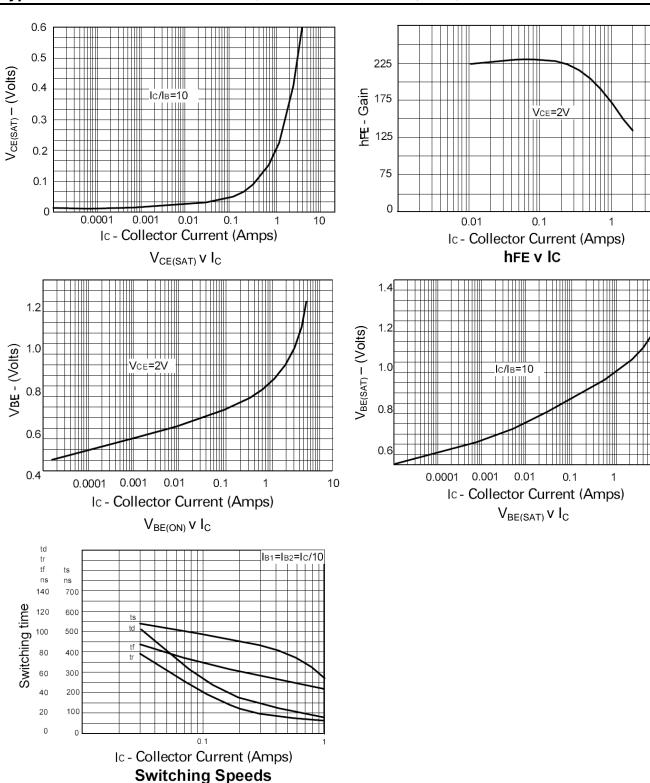
Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

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# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

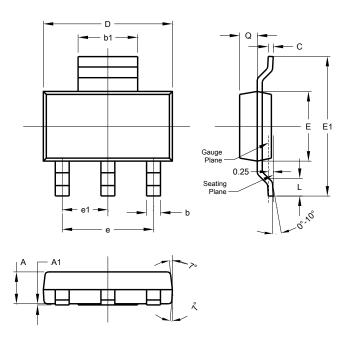




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**

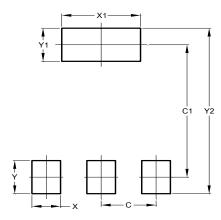


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Ø	0.84	0.94	0.89		
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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